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9 The semiconductor device of claim 1 wherein the third dielectric layer comprises etch stop material.

- 15 The method of claim 14 wherein the third dielectric layer material and the first and second etch stop materials are the same material.
- 16 The method of claim 14 wherein forming the second pad of the second etch stop material comprises:
- forming a layer of the second etch stop material on the device;
 - selectively removing the layer of the second etch stop material to leave the second pad of the second etch stop material over the stud.
- 17 The method of claim 10 wherein the step of removing removes a top portion of the stud to further expose the second dielectric layer at the top of the stud.

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